

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

**Claim 1. (withdrawn)** A metallic material for an electronic component, said metallic material consisting of an alloy including mainly Cu and having a composition of Mo in an amount of 0.1 to 3.0% by weight, a plurality of elements selected from the group consisting of Al, Au, Ag, Ti, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content.

**Claim 2. (currently amended)** A sputtering target material consisting essentially of a binary alloy including Cu and Mo in an amount of 0.1 to 3.0% by weight.

**Claim 3. (withdrawn)** A metallic material for electronic components, said metallic material consisting of an alloy including mainly Cu and having a composition of one or a plurality of elements selected from the group consisting of Cr, Ta, W and Ti in a total amount of 0.1 to 3.0% by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content.

**Claim 4. (withdrawn)** The metallic material for an electronic component according to one of claims 1 to 3, said metallic material having electrical resistance lower than  $10 \mu \Omega \text{ cm}$ .

**Claim 5. (withdrawn)** A metallic material for an electronic component, said metallic material consisting of a ternary alloy including mainly of Cu, Mo in an amount of 0.1 to 3.0% by weight and one element selected from the group consisting of Al, Au, Ag, Ti, Ni, Co and Si in an amount of 0.1 to 3.0% by weight.

**Claim 6. (withdrawn)** The metallic material for an electronic component according to claim 5, said metallic material having

electrical resistance higher than  $1.5 \mu \Omega \text{ cm}$  and lower than  $7.0 \mu \Omega \text{ cm}$ .

**Claim 7. (withdrawn)** The metallic material for an electronic component according to one of claim 1, claim 2, claim 3 and claim 5, said metallic material being used as a material for any one of a wiring pattern, an electrode, a contact and a target for a sputtering process.

**Claim 8. (withdrawn)** An electronic component having a wiring pattern, an electrode or a contact using a metallic material, said metallic material consisting of an alloy including mainly Cu and having a composition of Mo in an amount of 0.1 to 3.0% by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ag, Ti, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content.

**Claim 9. (currently amended)** An electronic component having a wiring pattern, an electrode or a contact using a metallic material, said metallic material formed by a sputtering process using a sputtering target ~~material~~ consisting essentially of a

binary alloy including Cu and Mo in an amount of 0.1 to 3.0% by weight.

**Claim 10. (withdrawn)** An electronic component having a wiring pattern, an electrode or a contact using a metallic material, said metallic material consisting of an alloy including mainly Cu and having a composition of one or a plurality of elements selected from the group consisting of Cr, Ta, W and Ti in a total amount of 0.1 to 3.0% by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content.

**Claim 11. (withdrawn)** The electronic component according to one of claims 8 to 10, said electrical component having a wiring pattern, an electrode or a contact which are formed by an etching process using a solution including phosphoric acid and nitric acid.

**Claim 12. (withdrawn)** The electronic component according to one of claims 8 to 10, said electronic component having a wiring

pattern, an electrode or a contact which are formed by an etching process under a gas atmosphere including chlorine.

**Claim 13. (withdrawn)** The electronic component according to one of claims 8 to 10, said electronic component having a region other than a wiring pattern, an electrode and a contact, which are formed by an etching process under a gas atmosphere including fluorine.

**Claim 14. (withdrawn)** The electronic component according to one of claims 8 to 10, said electronic component having a wiring pattern, an electrode or a contact which are formed by a heat treatment in the range of the temperatures from 100°C to 750°C.

**Claim 15. (withdrawn)** The electronic component according to one of claims 8 to 10, said electronic components having a wiring pattern, an electrode or a contact which are formed on a backing layer made of one of Ti, W, Ta, Mo, indium tin oxide, titanium nitride, oxidation silicon and silicon nitride.

**Claim 16. (withdrawn)** The electronic component according to one of claims 8 to 10, said electronic component having a wiring

pattern, an electrode or a contact which are directly formed on a substrate made of one of glass or plastic resin.

**Claim 17. (withdrawn)** An electronic device having a wiring pattern, an electrode or a contact using a metallic material, said metallic material consisting of an alloy including mainly Cu and having a composition of Mo in an amount of 0.1 to 3.0 % by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ag, Ti, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content.

**Claim 18. (currently amended)** An electronic device having a wiring pattern, an electrode or a contact using a metallic material, said metallic material formed by a sputtering process using a sputtering target ~~material~~ consisting essentially of a binary alloy including Cu and Mo in an amount of 0.1 to 3.0 % by weight.

**Claim 19. (withdrawn)** An electronic device having a wiring pattern, an electrode or a contact using a metallic material, said metallic material consisting of an alloy including mainly Cu and having a composition of one or a plurality of elements

selected from the group consisting of Cr, Ta, W and Ti in a total amount of 0.1 to 3.0% by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content.

**Claim 20. (withdrawn)** The electronic device according to one of claims 17 to 19, said electronic device having a wiring pattern, an electrode or a contact which are formed by an etching process using a solution including phosphoric acid and nitric acid.

**Claim 21. (withdrawn)** The electronic device according to one of claims 17 to 19, said electronic device having a wiring pattern, an electrode or a contact which are formed by an etching process under a gas atmosphere including chlorine.

**Claim 22. (withdrawn)** The electronic device according to one of claims 17 to 19, said electronic device having a region other than a wiring pattern, an electrode and a contact, which are formed by an etching process under a gas atmosphere including fluorine.

**Claim 23. (withdrawn)** The electronic device according to one of claims 17 to 19, said electronic device having a wiring pattern, an electrode or a contact which are formed by a heat treatment in the range of the temperatures from 100°C to 750°.

**Claim 24. (withdrawn)** The electronic device according to one of claims 17 to 19, said electronic device having a wiring pattern, an electrode or a contact which are formed on a backing layer made of one of Ti, W, Ta, Mo, indium tin oxide, titanium nitride, oxidation silicon and silicon nitride.

**Claim 25. (withdrawn)** The electronic device according to one of claims 17 to 19, said electronic device having a wiring pattern, an electrode or a contact which are directly formed on a substrate made of one of glass or plastic resin.

**Claim 26. (withdrawn)** A working method of a metallic material, in which a metallic film consisting of an alloy including mainly Cu and having a composition of Mo in an amount of 0.1 to 3.0 % by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ag, Ti, Ni, Co and



Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content is etched by using a solution including phosphoric acid and nitric acid to form a wiring pattern, an electrode or a contact.

**Claim 27. (withdrawn)** A working method of a metallic material, in which a metallic film consisting of a binary alloy including mainly Cu and Mo in an amount of 0.1 to 3.0 % by weight is etched by using a solution including phosphoric acid and nitric acid to form a wiring pattern, an electrode or a contact.

**Claim 28. (withdrawn)** A working method of a metallic material, in which a metallic film consisting of an alloy including mainly Cu having a composition of one or a plurality of elements selected from the group consisting of Cr, Ta, W and Ti in a total amount of 0.1 to 3.0% by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content is etched by using a solution including phosphoric acid and nitric acid to form a wiring pattern, an electrode or a contact.

**Claim 29. (withdrawn)** A working method of a metallic material, in which a metallic film consisting of an alloy including mainly Cu and having a composition of Mo in an amount of 0.1 to 3.0 % by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ag, Ti, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content is etched under a gas atmosphere including hydrochloric acid to form a wiring pattern, an electrode or a contact.

**Claim 30. (withdrawn)** A working method of a metallic material, in which a metallic film consisting of a binary alloy including mainly of Cu and Mo in an amount of 0.1 to 3.0 % by weight is etched under a gas atmosphere including hydrochloric acid to form a wiring pattern, an electrode or a contact.

**Claim 31. (withdrawn)** A working method of a metallic material, in which a metallic film consisting of an alloy including mainly Cu and having a composition of one or a plurality of elements selected from the group consisting of Cr, Ta, W and Ti in a total amount of 0.1 to 3.0% by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ni, Co and Si in a

total amount of 0.1 to 3.0% by weight and Cu as a remaining content is etched under a gas atmosphere including hydrochloric acid to form a wiring pattern, an electrode or a contact.

**Claim 32. (withdrawn)** A manufacturing method of electronic component, in which a metallic film is consisted of an alloy including mainly Cu and having a composition of Mo in an amount of 0.1 to 3.0 % by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ag, Ti, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content, and a film other than said metallic film is worked by an etching process under a gas atmosphere including fluorine.

**Claim 33. (withdrawn)** A manufacturing method of an electronic component, in which a metallic film is consisted of a binary alloy including mainly Cu and Mo in an amount of 0.1 to 3.0 % by weight, and a film other than said metallic film is worked by an etching process under a gas atmosphere including fluorine.

**Claim 34. (withdrawn)** A manufacturing method of an electronic component, in which a metallic film is consisted of an alloy

including mainly Cu and having a composition of one or a plurality of elements selected from the group consisting of Cr, Ta, W and Ti in a total amount of 0.1 to 3.0% by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content, and a film other than said metallic film is worked by an etching process under a gas atmosphere including fluorine.

**Claim 35. (withdrawn)** A working method of a metallic material, in which a metallic film formed by said metallic material consisting of an alloy including mainly Cu and having a composition of Mo in an amount of 0.1 to 3.0 % by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ag, Ti, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content is subjected to a heat treatment in the range of temperatures from 100°C to 750°C to form a wiring pattern, an electrode or a contact.

**Claim 36. (withdrawn)** A working method of a metallic material, in which a metallic film formed by said metallic material consisting of a binary alloy including mainly Cu and Mo

in an amount of 0.1 to 3.0 % by weight is subjected to a heat treatment in a range of temperatures from 100°C to 750°C to form a wiring pattern, an electrode or a contact.

**Claim 37. (withdrawn)** A working method of a metallic material, in which a metallic film formed by said metallic material consisting of an alloy including mainly Cu and having a composition of one or a plurality of elements selected from the group consisting of Cr, Ta, W and Ti in a total amount of 0.1 to 3.0% by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ag, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content is subjected to a heat treatment in a range of temperatures from 100°C to 750°C to form a wiring pattern, an electrode or a contact.

**Claim 38. (withdrawn)** A working method of a metallic material, in which a metallic film formed by said metallic material consisting of an alloy including mainly Cu and having a composition of Mo in an amount of 0.1 to 3.0 % by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ag, Ti, Ni, Co and Si in a total amount of 0.1 to 3.0% by

weight and Cu as a remaining content is deposited on a backing layer made of one of Ti, W, Ta, Mo, indium tin oxide, titanium nitride, oxidation silicon and silicon nitride to form a wiring pattern, an electrode or a contact.

**Claim 39. (withdrawn)** A working method of a metallic material, in which a metallic film formed by said metallic material consisting of a binary alloy including mainly Cu and Mo in an amount of 0.1 to 3.0 % by weight is deposited on a backing layer made of one of Ti, W, Ta, Mo, indium tin oxide, titanium nitride, oxidation silicon and silicon nitride to form a wiring pattern, an electrode or a contact.

**Claim 40. (withdrawn)** A working method of a metallic material, in which a metallic film formed by said metallic material consisting of an alloy including mainly Cu and having a composition of one or a plurality of elements selected from the group consisting of Cr, Ta, W and Ti in a total amount of 0.1 to 3.0% by weigh, one or a plurality of elements selected from the group consisting of Al, Au, Ag, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content is deposited on a backing layer made of one of Ti, W, Ta, Mo, indium

tin oxide, titanium nitride, oxidation silicon and silicon nitride to form a wiring pattern, an electrode or a contact.

**Claim 41. (withdrawn)** A working method of a metallic material, in which a metallic film formed by said metallic material consisting of an alloy including mainly Cu and having a composition of Mo in an amount of 0.1 to 3.0 % by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ag, Ti, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content is directly deposited on a substrate made of glass or resin such as plastic to form a wiring pattern, an electrode or a contact.

**Claim 42. (withdrawn)** A working method of a metallic material, in which a metallic film formed by said metallic material consisting of a binary alloy including mainly Cu and Mo in an amount of 0.1 to 3.0 % by weight is directly deposited on a substrate made of glass or resin such as plastic to form a wiring pattern, an electrode or a contact.

**Claim 43. (withdrawn)** A working method of a metallic material, in which a metallic film formed by said metallic

material consisting of an alloy including mainly Cu and having a composition of one or a plurality of elements selected from the group consisting of Cr, Ta, W and Ti in a total amount of 0.1 to 3.0% by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content is directly deposited on a substrate made of glass or resin such as plastic to form a wiring pattern, an electrode or a contact.

**Claim 44. (withdrawn)** An electronic optical component having reflective film, an electrode or a wiring pattern which are formed by a metallic film consisting of an alloy including mainly Cu and having a content of Mo in an amount of 0.1 to 3.0 % by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ag, Ti, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content.

**Claim 45. (currently amended)** An electronic optical component having reflective film, an electrode or a wiring pattern which are formed by a metallic film formed by a sputtering process using a sputtering target ~~material~~ consisting essentially of a



binary alloy including Cu and Mo in an amount of 0.1 to 3.0 % by weight.

**Claim 46. (withdrawn)** An electronic optical component having reflective film, an electrode or a wiring pattern which are formed by a metallic film consisting of an alloy including mainly Cu and having a composition of one or a plurality of elements selected from the group consisting of Cr, Ta, W and Ti in a total amount of 0.1 to 3.0% by weight, one or a plurality of elements selected from the group consisting of Al, Au, Ni, Co and Si in a total amount of 0.1 to 3.0% by weight and Cu as a remaining content.